



#### MAXIMUM RATINGS (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>C</sub>	600	mA
Power Dissipation	P <sub>D</sub>	1.2	W
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	Θ <sub>JA</sub>	104	°C/W

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =50V		10	nA
I <sub>CBO</sub>	V <sub>CB</sub> =50V, T <sub>A</sub> =125°C		10	µA
I <sub>CEV</sub>	V <sub>CE</sub> =30V, V <sub>BE</sub> =0.5V		50	nA
BV <sub>CBO</sub>	I <sub>C</sub> =10µA	60		V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA	60		V
BV <sub>EBO</sub>	I <sub>E</sub> =10µA	5.0		V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		0.4	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		1.6	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		1.3	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA		2.6	V
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.1mA	75		
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1.0mA	100		
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	100		
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =150mA	100	300	

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

#### DESCRIPTION:

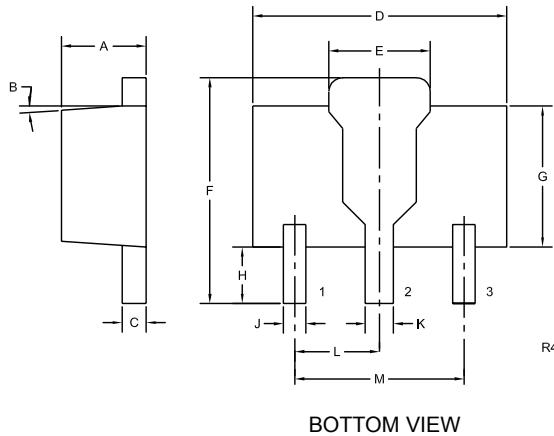
The CENTRAL SEMICONDUCTOR CXT2907A type is a PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

#### MARKING CODE: FULL PART NUMBER

ELECTRICAL CHARACTERISTICS (Continued)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$h_{FE}$	$V_{CE}=10V, I_C=500mA$	50		
$f_T$	$V_{CE}=20V, I_C=50mA, f=100MHz$	200		MHz
$C_{ob}$	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
$C_{ib}$	$V_{BE}=2.0V, I_C=0, f=1.0MHz$		30	pF
$t_{on}$	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		45	ns
$t_d$	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		10	ns
$t_r$	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		40	ns
$t_{off}$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		100	ns
$t_s$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		80	ns
$t_f$	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		30	ns

SOT-89 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	$4^\circ$		$4^\circ$	
C	0.014	0.018	0.35	0.46
D	0.173	0.185	4.40	4.70
E	0.064	0.074	1.62	1.87
F	0.146	0.177	3.70	4.50
G	0.090	0.106	2.29	2.70
H	0.028	0.051	0.70	1.30
J	0.014	0.019	0.36	0.48
K	0.017	0.023	0.44	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R4)

MARKING CODE:  
FULL PART NUMBER

LEAD CODE:

- 1) Emitter
- 2) Collector
- 3) Base